N-Channel Super Junction Power MOSFET Ⅲ

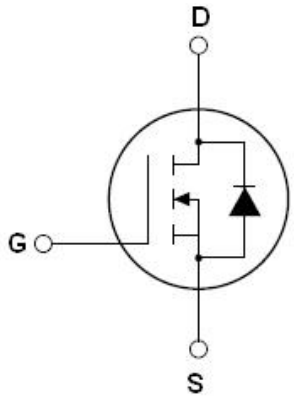
General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

$V_{DS\ min@Tjmax}$	710	V
$R_{DS(ON)TYP}$	90	mΩ
ID	36	A
Qg	45	nC

Features

- Optimized body diode reverse recovery performance
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

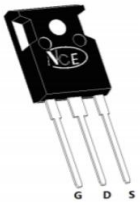


Schematic diagram

Application

- Power factor correction（PFC）
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply（UPS）
- LLC Half-bridge

✧ **Intrinsic fast-recovery body diode**



TO-247

Package Marking And Ordering Information

Device	Device Package	Marking
NCE65NF099T	TO-247	NCE65NF099T

Table 1. Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V_{GS}=0V）	V_{DS}	650	V
Gate-Source Voltage (V_{DS}=0V) AC (f>1 Hz)	V_{GS}	±30	V
Continuous Drain Current at Tc=25°C	$I_{D\ (DC)}$	36	A
Continuous Drain Current at Tc=100°C	$I_{D\ (DC)}$	25.2	A
Pulsed drain current **(Note 1)**	$I_{DM\ (pluse)}$	108	A
Maximum Power Dissipation(Tc=25℃) Derate above 25°C	P_D	346 2.30	W W/°C
Single pulse avalanche energy **(Note 2)**	E_{AS}	841	mJ
Avalanche current**(Note 1)**	I_{AR}	7	A
Repetitive Avalanche energy ， t_{AR} limited by T_{jmax} **(Note 1)**	E_{AR}	3.9	mJ

Parameter	Symbol	Value	Unit
Drain Source voltage slope, V_{DS} ≤480 V,	dv/dt	50	V/ns
Reverse diode dv/dt， V_{DS} ≤480 V,I_{SD}<I_D	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55...+175	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance，Junction-to-Case（Maximum）	R_{thJC}	0.43	°C /W
Thermal Resistance，Junction-to-Ambient （Maximum）	R_{thJA}	62	°C /W

Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=500μA	650			V
Zero Gate Voltage Drain Current(Tc=25℃)	I_{DSS}	V_{DS}=650V,V_{GS}=0V			10	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I_{DSS}	V_{DS}=650V,V_{GS}=0V			200	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	3	4	5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=18A		90	99	mΩ
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1.0MHz		2400	2800	pF
Output Capacitance	C_{oss}			82		pF
Reverse Transfer Capacitance	C_{rss}			1.3		pF
Total Gate Charge	Q_g	V_{DS}=480V,I_D=18A, V_{GS}=10V		45	55	nC
Gate-Source Charge	Q_{gs}			26		nC
Gate-Drain Charge	Q_{gd}			7		nC
Intrinsic gate resistance	R_G	f = 1 MHz open drain		1		Ω
Switching times						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=380V,I_D=18A, R_G=1.7Ω,V_{GS}=10V		15		nS
Turn-on Rise Time	t_r			14		nS
Turn-Off Delay Time	$t_{d(off)}$			72		nS
Turn-Off Fall Time	t_f			14		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	T_C=25°C			36	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				108	A
Forward On Voltage	V_{SD}	Tj=25°C,I_{SD}=36A,V_{GS}=0V		0.9	1.2	V
Reverse Recovery Time	t_{rr}	Tj=25°C,I_F=18A,di/dt=100A/μs		170		nS
Reverse Recovery Charge	Q_{rr}			1.5		uC
Peak Reverse Recovery Current	I_{rrm}			17		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25℃,VDD=50V,VG=10V, R_G=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

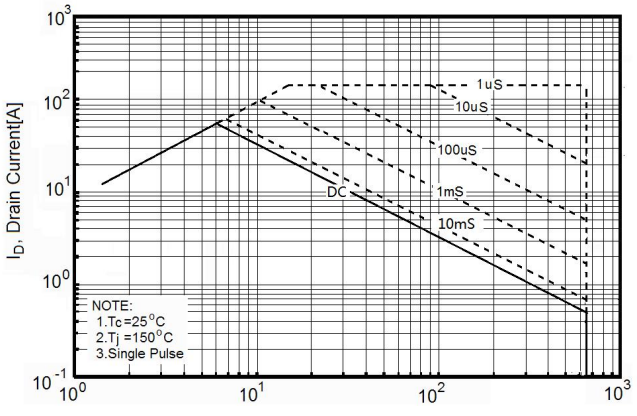


Figure2. Capacitance

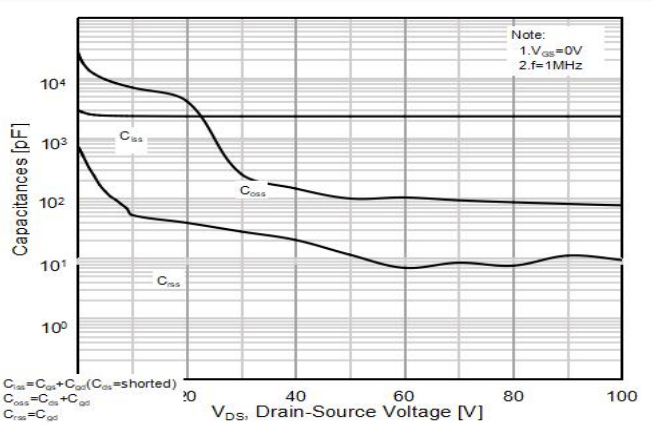


Figure3. Output characteristics

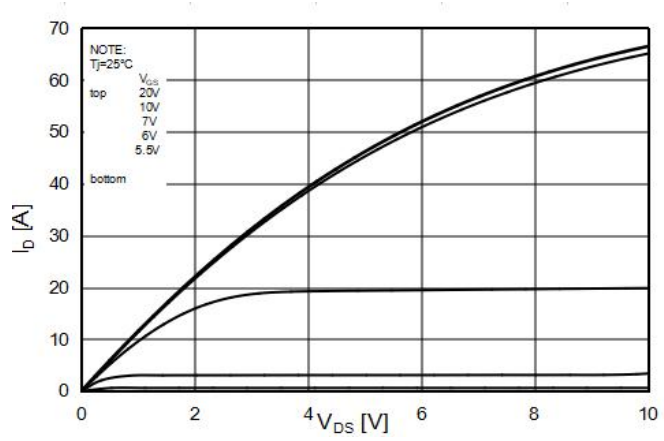


Figure4. Source-Drain Diode Forward Voltage

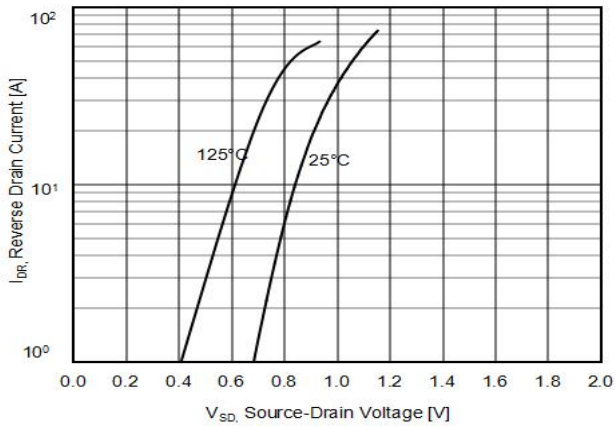


Figure5. Static drain-source on resistance

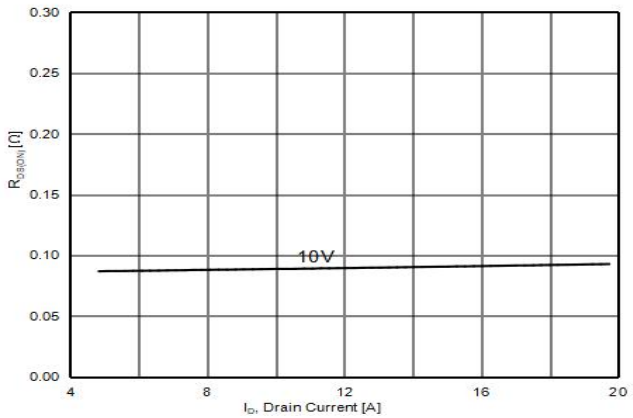


Figure6. Transfer characteristics

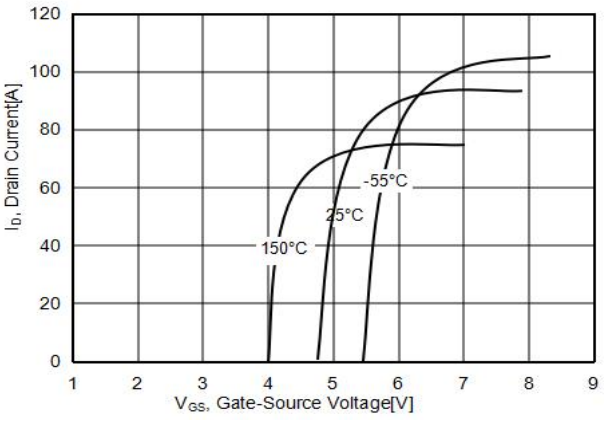


Figure7. $R_{DS(ON)}$ vs Junction Temperature

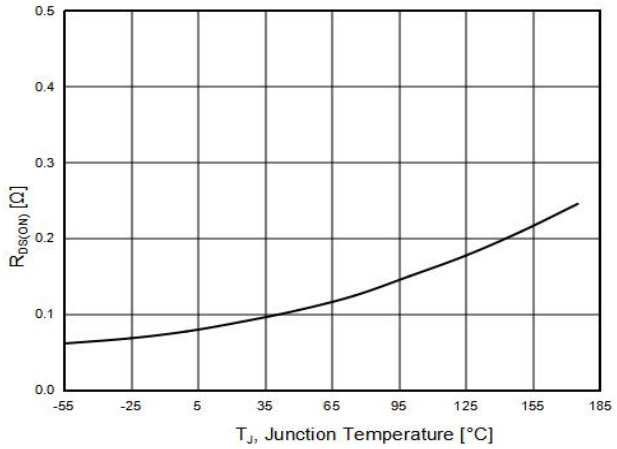


Figure8. BV_{DSS} vs Junction Temperature

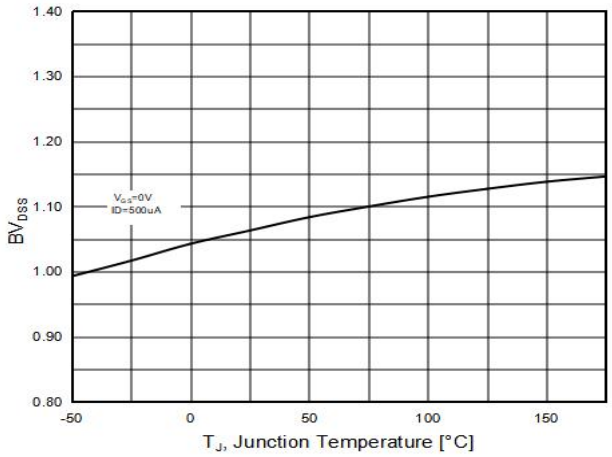


Figure9. Gate charge waveforms

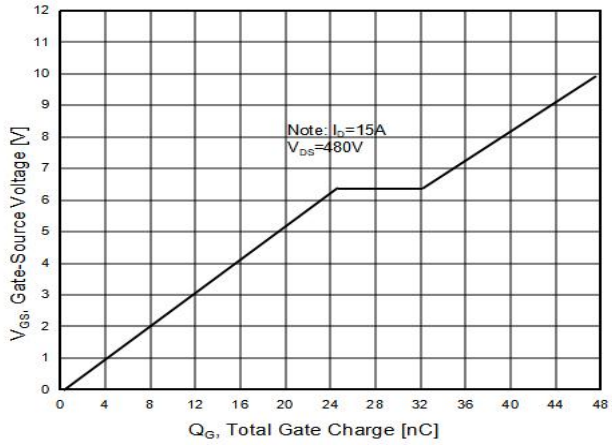
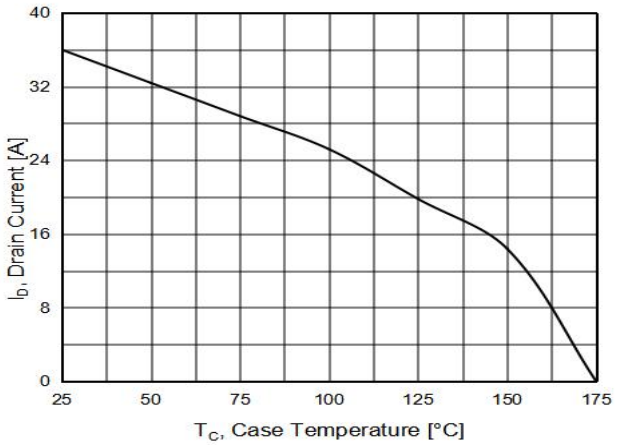
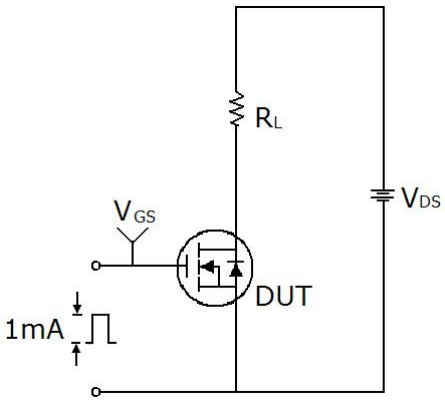


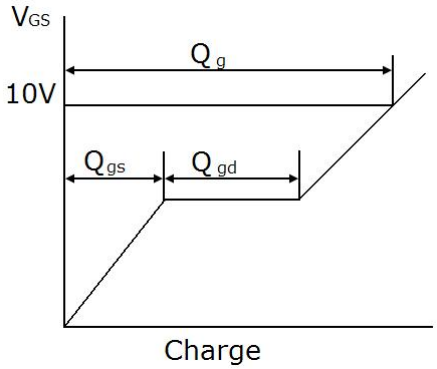
Figure10. Maximum I_D vs Junction Temperature



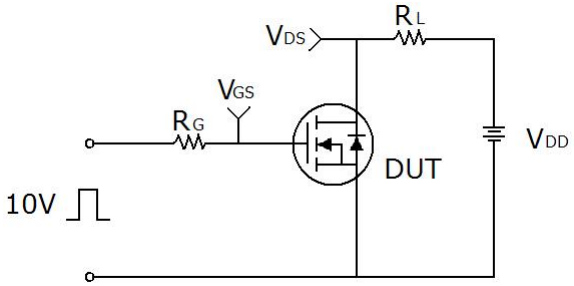
Test circuit

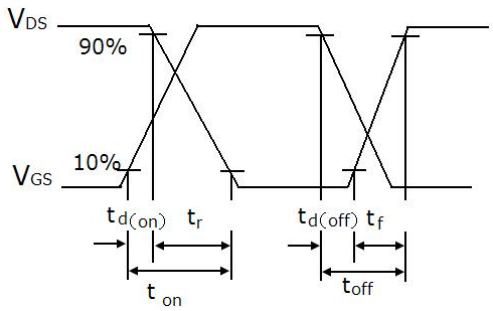
1）Gate charge test circuit & Waveform



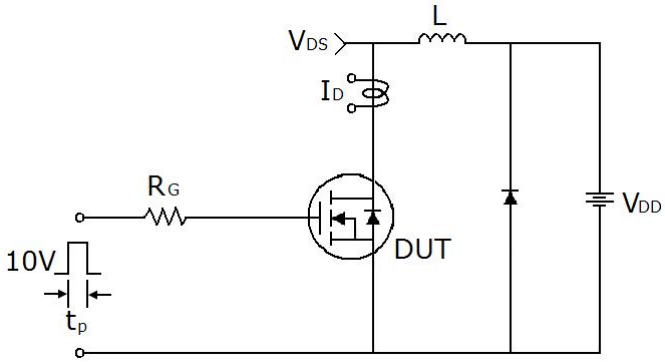


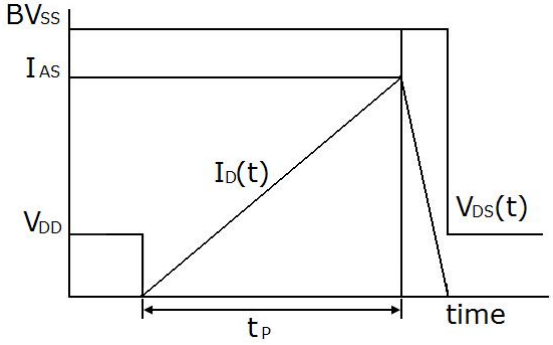
2）Switch Time Test Circuit：



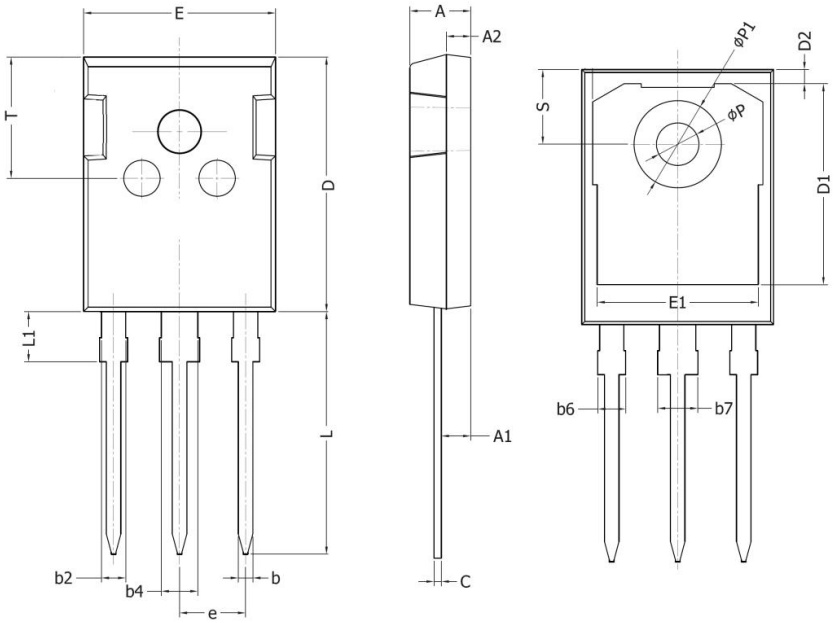


3）Unclamped Inductive Switching Test Circuit & Waveforms



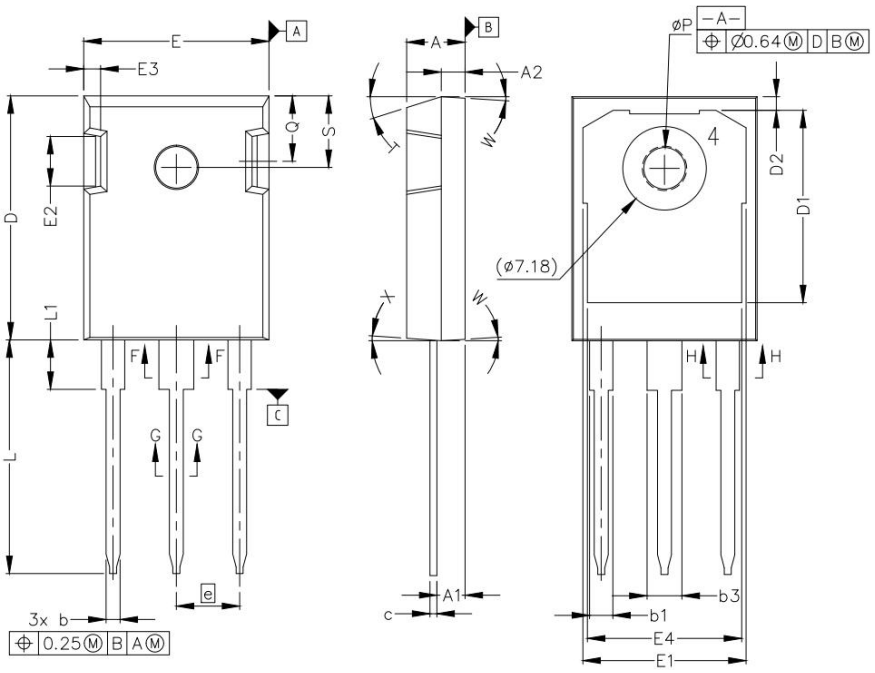


TO-247 （P）Package Information



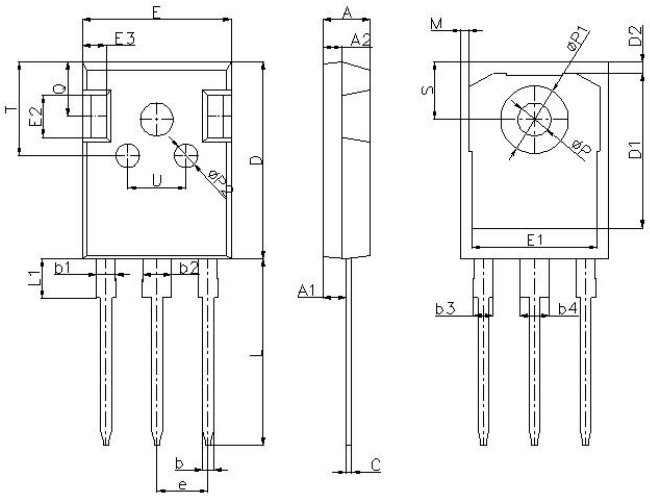
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.193	0.201
A1	2.31	2.51	0.091	0.099
A2	1.90	2.10	0.075	0.083
b	1.16	1.26	0.046	0.050
b2	1.96	2.06	0.077	0.081
b4	2.96	3.06	0.117	0.120
b6	-	2.25	-	0.089
b7	-	3.25	-	0.128
C	0.59	0.66	0.023	0.026
D	20.90	21.10	0.823	0.831
D1	16.25	16.85	0.640	0.663
D2	1.05	1.35	0.041	0.053
E	15.70	15.90	0.618	0.626
E1	13.10	13.50	0.516	0.531
e	5.436 BSC		0.214 BSC	
L	19.80	20.10	0.780	0.791
L1	-	4.30	-	0.169
P	3.40	3.60	0.134	0.142
P1	7.00	7.40	0.276	0.291
S	6.05	6.25	0.238	0.246
T	9.80	10.20	0.386	0.402

TO-247-B Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	0.190	0.205
A1	2.29	2.54	0.090	0.100
A2	1.91	2.16	0.075	0.085
b	1.07	1.33	0.042	0.052
b1	1.91	2.41	0.075	0.095
b3	2.87	3.38	0.113	0.133
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.25	0.037	0.049
E	15.75	16.13	0.620	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	1.90	0.039	0.075
E4	12.38	13.43	0.487	0.529
e	5.44 BSC		0.214 BSC	
N	3.00		0.118	
L	19.81	20.32	0.780	0.800
L1	4.10	4.40	0.161	0.173
P	3.51	3.65	0.138	0.144
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

TO-247-E Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.193	0.201
A1	2.31	2.51	0.091	0.099
A2	1.90	2.10	0.075	0.083
b	1.16	1.26	0.046	0.050
b1	1.96	2.06	0.077	0.081
b2	2.96	3.06	0.117	0.120
b3	-	2.25	-	0.089
b4	-	3.25	-	0.128
C	0.59	0.66	0.023	0.026
D	20.90	21.10	0.823	0.831
D1	16.25	16.85	0.640	0.663
D2	1.05	1.35	0.041	0.053
E	15.70	15.90	0.618	0.626
E1	13.10	13.50	0.516	0.531
E2	4.40	4.60	0.173	0.181
E3	2.40	2.60	0.094	0.102
e	5.436BSC		0.214BSC	
L	19.80	20.10	0.780	0.791
L1	-	4.30	-	0.169
M	0.35	0.95	0.014	0.037
P	3.40	3.60	0.134	0.142
P1	7.00	7.40	0.276	0.291
P2	2.40	2.60	0.094	0.102
Q	5.60	6.00	0.220	0.236
S	6.05	6.25	0.238	0.246
T	9.80	10.20	0.386	0.402
U	6.00	6.40	0.236	0.252

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